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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f072cbu7

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Table 2. STM32F072x8/xB family device features and peripheral counts

Peripheral	STM32F072Cx	STM32F072Rx	STM32F072Vx	
Flash memory (Kbyte)	64	128	64	
SRAM (Kbyte)	16			
Timers	Advanced control	1 (16-bit)		
	General purpose	5 (16-bit) 1 (32-bit)		
	Basic	2 (16-bit)		
Comm. interfaces	SPI [I^2S] ⁽¹⁾	2 [2]		
	I^2C	2		
	USART	4		
	CAN	1		
	USB	1		
	CEC	1		
12-bit ADC (number of channels)	1 (10 ext. + 3 int.)	1 (16 ext. + 3 int.)		
12-bit DAC (number of channels)	1 (2)			
Analog comparator	2			
GPIOs	37	51	87	
Capacitive sensing channels	17	18	24	
Max. CPU frequency	48 MHz			
Operating voltage	2.0 to 3.6 V			
Operating temperature	Ambient operating temperature: -40°C to 85°C / -40°C to 105°C Junction temperature: -40°C to 105°C / -40°C to 125°C			
Packages	LQFP48 UFQFPN48 WLCSP49	LQFP64 UFBGA64	LQFP100 UFBGA100	

1. The SPI interface can be used either in SPI mode or in I^2S audio mode.

Table 6. Number of capacitive sensing channels available on STM32F072x8/xB devices

Analog I/O group	Number of capacitive sensing channels		
	STM32F072Vx	STM32F072Rx	STM32F072Cx
G1	3	3	3
G2	3	3	3
G3	3	3	2
G4	3	3	3
G5	3	3	3
G6	3	3	3
G7	3	0	0
G8	3	0	0
Number of capacitive sensing channels	24	18	17

3.14 Timers and watchdogs

The STM32F072x8/xB devices include up to six general-purpose timers, two basic timers and an advanced control timer.

Table 7 compares the features of the different timers.

Table 7. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	3
General purpose	TIM2	32-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM3	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM14	16-bit	Up	integer from 1 to 65536	No	1	-
	TIM15	16-bit	Up	integer from 1 to 65536	Yes	2	1
	TIM16 TIM17	16-bit	Up	integer from 1 to 65536	Yes	1	1
Basic	TIM6 TIM7	16-bit	Up	integer from 1 to 65536	Yes	-	-

Table 13. STM32F072x8/xB pin definitions (continued)

Pin numbers						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	LQFP48/UQFPN48	WL CSP49					Alternate functions	Additional functions
C10	79	B6	52	-	-	PC11	I/O	FT	(3)	USART3_RX, USART4_RX	-
B10	80	C5	53	-	-	PC12	I/O	FT	(3)	USART3_CK, USART4_CK	-
C9	81	-	-	-	-	PD0	I/O	FT	(3)	SPI2_NSS, I2S2_WS, CAN_RX	-
B9	82	-	-	-	-	PD1	I/O	FT	(3)	SPI2_SCK, I2S2_CK, CAN_TX	-
C8	83	B5	54	-	-	PD2	I/O	FT	(3)	USART3_RTS, TIM3_ETR	-
B8	84	-	-	-	-	PD3	I/O	FT	-	SPI2_MISO, I2S2_MCK, USART2_CTS	-
B7	85	-	-	-	-	PD4	I/O	FT	-	SPI2_MOSI, I2S2_SD, USART2_RTS	-
A6	86	-	-	-	-	PD5	I/O	FT	-	USART2_TX	-
B6	87	-	-	-	-	PD6	I/O	FT	-	USART2_RX	-
A5	88	-	-	-	-	PD7	I/O	FT	-	USART2_CK	-
A8	89	A5	55	39	A3	PB3	I/O	FT	-	SPI1_SCK, I2S1_CK, TIM2_CH2, TSC_G5_IO1, EVENTOUT	-
A7	90	A4	56	40	A4	PB4	I/O	FT	-	SPI1_MISO, I2S1_MCK, TIM17_BKIN, TIM3_CH1, TSC_G5_IO2, EVENTOUT	-
C5	91	C4	57	41	B4	PB5	I/O	FT	-	SPI1_MOSI, I2S1_SD, I2C1_SMBA, TIM16_BKIN, TIM3_CH2	WKUP6
B5	92	D3	58	42	C4	PB6	I/O	FTf	-	I2C1_SCL, USART1_TX, TIM16_CH1N, TSC_G5_IO3	-

Table 14. Alternate functions selected through GPIOA_AFR registers for port A

Pin name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PA0	-	USART2_CTS	TIM2_CH1_ETR	TSC_G1_IO1	USART4_TX	-	-	COMP1_OUT
PA1	EVENTOUT	USART2_RTS	TIM2_CH2	TSC_G1_IO2	USART4_RX	TIM15_CH1N	-	-
PA2	TIM15_CH1	USART2_TX	TIM2_CH3	TSC_G1_IO3	-	-	-	COMP2_OUT
PA3	TIM15_CH2	USART2_RX	TIM2_CH4	TSC_G1_IO4	-	-	-	-
PA4	SPI1_NSS, I2S1_WS	USART2_CK	-	TSC_G2_IO1	TIM14_CH1	-	-	-
PA5	SPI1_SCK, I2S1_CK	CEC	TIM2_CH1_ETR	TSC_G2_IO2	-	-	-	-
PA6	SPI1_MISO, I2S1_MCK	TIM3_CH1	TIM1_BKIN	TSC_G2_IO3	USART3_CTS	TIM16_CH1	EVENTOUT	COMP1_OUT
PA7	SPI1_MOSI, I2S1_SD	TIM3_CH2	TIM1_CH1N	TSC_G2_IO4	TIM14_CH1	TIM17_CH1	EVENTOUT	COMP2_OUT
PA8	MCO	USART1_CK	TIM1_CH1	EVENTOUT	CRS_SYNC	-	-	-
PA9	TIM15_BKIN	USART1_TX	TIM1_CH2	TSC_G4_IO1	-	-	-	-
PA10	TIM17_BKIN	USART1_RX	TIM1_CH3	TSC_G4_IO2	-	-	-	-
PA11	EVENTOUT	USART1_CTS	TIM1_CH4	TSC_G4_IO3	CAN_RX	-	-	COMP1_OUT
PA12	EVENTOUT	USART1_RTS	TIM1_ETR	TSC_G4_IO4	CAN_TX	-	-	COMP2_OUT
PA13	SWDIO	IR_OUT	USB_NOE	-	-	-	-	-
PA14	SWCLK	USART2_TX	-	-	-	-	-	-
PA15	SPI1_NSS, I2S1_WS	USART2_RX	TIM2_CH1_ETR	EVENTOUT	USART4_RTS	-	-	-

Table 29. Typical and maximum current consumption from V_{DD} supply at V_{DD} = 3.6 V (continued)

Symbol	Parameter	Conditions	f _{HCLK}	All peripherals enabled ⁽¹⁾			All peripherals disabled			Unit	
				Typ	Max @ T _A ⁽²⁾			Typ	Max @ T _A ⁽²⁾		
					25 °C	85 °C	105 °C		25 °C	85 °C	
I _{DD}	Supply current in Run mode, code executing from RAM	HSI48	48 MHz	23.1	25.4	25.8	26.6	12.8	13.5	13.7	13.9
		HSE bypass, PLL on	48 MHz	23.0	25.3 ⁽³⁾	25.7	26.5 ⁽³⁾	12.6	13.3 ⁽³⁾	13.5	13.8 ⁽³⁾
			32 MHz	15.4	17.3	17.8	18.3	7.96	8.92	9.17	9.73
			24 MHz	11.4	12.9	13.5	13.7	6.48	8.04	8.23	8.41
		HSE bypass, PLL off	8 MHz	4.21	4.6	4.89	5.25	2.07	2.3	2.35	2.94
			1 MHz	0.78	0.9	0.92	1.15	0.36	0.48	0.59	0.82
		HSI clock, PLL on	48 MHz	23.1	24.5	25.0	25.2	12.6	13.7	13.9	14.0
			32 MHz	15.4	17.4	17.7	18.2	8.05	8.85	9.16	9.94
			24 MHz	11.5	13.0	13.6	13.9	6.49	8.06	8.21	8.47
	Supply current in Sleep mode	HSI clock, PLL off	8 MHz	4.34	4.75	5.03	5.41	2.11	2.36	2.38	2.98
		HSE bypass, PLL on	HSI48	48 MHz	15.1	16.6	16.8	17.5	3.08	3.43	3.56
			48 MHz	15.0	16.5 ⁽³⁾	16.7	17.3 ⁽³⁾	2.93	3.28 ⁽³⁾	3.41	3.46 ⁽³⁾
			32 MHz	9.9	11.4	11.6	11.9	2.0	2.24	2.32	2.49
			24 MHz	7.43	8.17	8.71	8.82	1.63	1.82	1.88	1.9
		HSE bypass, PLL off	8 MHz	2.83	3.09	3.26	3.66	0.76	0.88	0.91	0.93
			1 MHz	0.42	0.54	0.55	0.67	0.28	0.39	0.41	0.43
		HSI clock, PLL on	48 MHz	15.0	17.2	17.3	17.9	3.04	3.37	3.41	3.46
			32 MHz	9.93	11.3	11.6	11.7	2.11	2.35	2.44	2.65
			24 MHz	7.53	8.45	8.87	8.95	1.64	1.83	1.9	1.93
		HSI clock, PLL off	8 MHz	2.95	3.24	3.41	3.8	0.8	0.92	0.94	0.97

1. USB is kept disabled as this IP functions only with a 48 MHz clock.
2. Data based on characterization results, not tested in production unless otherwise specified.
3. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

Table 32. Typical and maximum current consumption from the V_{BAT} supply

Symbol	Parameter	Conditions	Typ @ V _{BAT}						Max ⁽¹⁾			Unit
			1.65 V	1.8 V	2.4 V	2.7 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD_VBAT}	RTC domain supply current	LSE & RTC ON; "Xtal mode": lower driving capability; LSEDRV[1:0] = '00'	0.5	0.6	0.7	0.8	1.1	1.2	1.3	1.7	2.3	µA
		LSE & RTC ON; "Xtal mode" higher driving capability; LSEDRV[1:0] = '11'	0.8	0.9	1.1	1.2	1.4	1.6	1.7	2.1	2.8	

1. Data based on characterization results, not tested in production.

Typical current consumption

The MCU is placed under the following conditions:

- V_{DD} = V_{DDA} = 3.3 V
- All I/O pins are in analog input configuration
- The Flash memory access time is adjusted to f_{HCLK} frequency:
 - 0 wait state and Prefetch OFF from 0 to 24 MHz
 - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled, f_{PCLK} = f_{HCLK}
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8 and 16 is used for the frequencies 4 MHz, 2 MHz, 1 MHz and 500 kHz respectively

trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see [Table 35: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 34. Switching output I/O current consumption

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{sw})	Typ	Unit
I _{SW}	I/O current consumption	V _{DDIOX} = 3.3 V C = C _{INT}	4 MHz	0.07	mA
			8 MHz	0.15	
			16 MHz	0.31	
			24 MHz	0.53	
			48 MHz	0.92	
		V _{DDIOX} = 3.3 V C _{EXT} = 0 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.18	
			8 MHz	0.37	
			16 MHz	0.76	
			24 MHz	1.39	
			48 MHz	2.188	
		V _{DDIOX} = 3.3 V C _{EXT} = 10 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.32	
			8 MHz	0.64	
			16 MHz	1.25	
			24 MHz	2.23	
			48 MHz	4.442	
		V _{DDIOX} = 3.3 V C _{EXT} = 22 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.49	
			8 MHz	0.94	
			16 MHz	2.38	
			24 MHz	3.99	
		V _{DDIOX} = 3.3 V C _{EXT} = 33 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.64	
			8 MHz	1.25	
			16 MHz	3.24	
			24 MHz	5.02	
		V _{DDIOX} = 3.3 V C _{EXT} = 47 pF C = C _{INT} + C _{EXT} + C _S C = C _{int}	4 MHz	0.81	
			8 MHz	1.7	
			16 MHz	3.67	
		V _{DDIOX} = 2.4 V C _{EXT} = 47 pF C = C _{INT} + C _{EXT} + C _S C = C _{int}	4 MHz	0.66	
			8 MHz	1.43	
			16 MHz	2.45	
			24 MHz	4.97	

1. C_S = 7 pF (estimated value).

Table 35. Peripheral current consumption (continued)

Peripheral	Typical consumption at 25 °C	Unit
APB	APB-Bridge ⁽²⁾	2.8
	ADC ⁽³⁾	4.1
	CAN	12.4
	CEC	1.5
	CRS	0.8
	DAC ⁽³⁾	4.7
	DEBUG (MCU debug feature)	0.1
	I2C1	3.9
	I2C2	4.0
	PWR	1.3
	SPI1	8.7
	SPI2	8.5
	SYSCFG & COMP	1.7
	TIM1	14.9
	TIM2	15.5
	TIM3	11.4
	TIM6	2.5
	TIM7	2.3
	TIM14	5.3
	TIM15	9.1
	TIM16	6.6
	TIM17	6.8
	USART1	17.0
	USART2	16.7
	USART3	5.4
	USART4	5.4
	USB	7.2
	WWDG	1.4
All APB peripherals		182

- 1. The BusMatrix is automatically active when at least one master is ON (CPU, DMA).
- 2. The APB Bridge is automatically active when at least one peripheral is ON on the Bus.
- 3. The power consumption of the analog part (I_{DDA}) of peripherals such as ADC, DAC, Comparators, is not included. Refer to the tables of characteristics in the subsequent sections.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
			8/48 MHz	8/48 MHz	
S _{EMI}	Peak level	V _{DD} = 3.6 V, T _A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	-2	dB μ V
			30 to 130 MHz	27	
			130 MHz to 1 GHz	17	
			EMI Level	4	

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 53. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{lkg}	Input leakage current ⁽²⁾	TC, FT and FTf I/O TTa in digital mode $V_{SS} \leq V_{IN} \leq V_{DDIOx}$	-	-	± 0.1	μA
		TTa in digital mode $V_{DDIOx} \leq V_{IN} \leq V_{DDA}$	-	-	1	
		TTa in analog mode $V_{SS} \leq V_{IN} \leq V_{DDA}$	-	-	± 0.2	
		FT and FTf I/O $V_{DDIOx} \leq V_{IN} \leq 5 V$	-	-	10	
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	25	40	55	$k\Omega$
R_{PD}	Weak pull-down equivalent resistor ⁽³⁾	$V_{IN} = -V_{DDIOx}$	25	40	55	$k\Omega$
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Data based on design simulation only. Not tested in production.
2. The leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 52: I/O current injection susceptibility](#).
3. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in [Figure 22](#) for standard I/Os, and in [Figure 23](#) for 5 V-tolerant I/Os. The following curves are design simulation results, not tested in production.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/- 8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DDIOx} , plus the maximum consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 21: Voltage characteristics](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} , plus the maximum consumption of the MCU sunk on V_{SS} , cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 21: Voltage characteristics](#)).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 24: General operating conditions](#). All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 54. Output voltage characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ $ I_{IO} = 8 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		$V_{DDIOx}-0.4$	-	
V_{OL}	Output low level voltage for an I/O pin	TTL port ⁽²⁾ $ I_{IO} = 8 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		2.4	-	
$V_{OL}^{(3)}$	Output low level voltage for an I/O pin	$ I_{IO} = 20 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	1.3	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DDIOx}-1.3$	-	
$V_{OL}^{(3)}$	Output low level voltage for an I/O pin	$ I_{IO} = 6 \text{ mA}$ $V_{DDIOx} \geq 2 \text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DDIOx}-0.4$	-	
$V_{OL}^{(4)}$	Output low level voltage for an I/O pin	$ I_{IO} = 4 \text{ mA}$	-	0.4	V
$V_{OH}^{(4)}$	Output high level voltage for an I/O pin		$V_{DDIOx}-0.4$	-	V
$V_{OLFm+}^{(3)}$	Output low level voltage for an FTf I/O pin in Fm+ mode	$ I_{IO} = 20 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	0.4	V
			$ I_{IO} = 10 \text{ mA}$	-	0.4

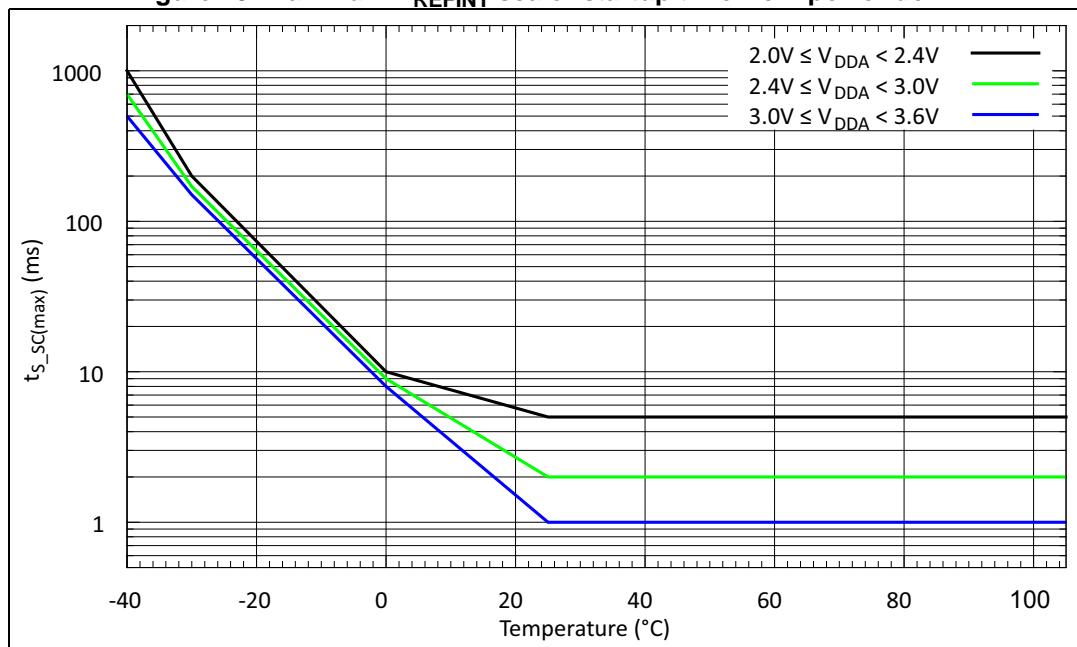
1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in [Table 21: Voltage characteristics](#), and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO} .
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Data based on characterization results. Not tested in production.
4. Data based on characterization results. Not tested in production.

Table 61. Comparator characteristics (continued)

Symbol	Parameter	Conditions		Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V_{hys}	Comparator hysteresis	No hysteresis (COMPxHYST[1:0]=00)	-	-	0	-	mV
		Low hysteresis (COMPxHYST[1:0]=01)	High speed mode	3	8	13	
			All other power modes	5		10	
		Medium hysteresis (COMPxHYST[1:0]=10)	High speed mode	7	15	26	
			All other power modes	9		19	
		High hysteresis (COMPxHYST[1:0]=11)	High speed mode	18	31	49	
			All other power modes	19		40	

1. Data based on characterization results, not tested in production.

2. For more details and conditions see [Figure 29: Maximum \$V_{\text{REFINT}}\$ scaler startup time from power down](#).

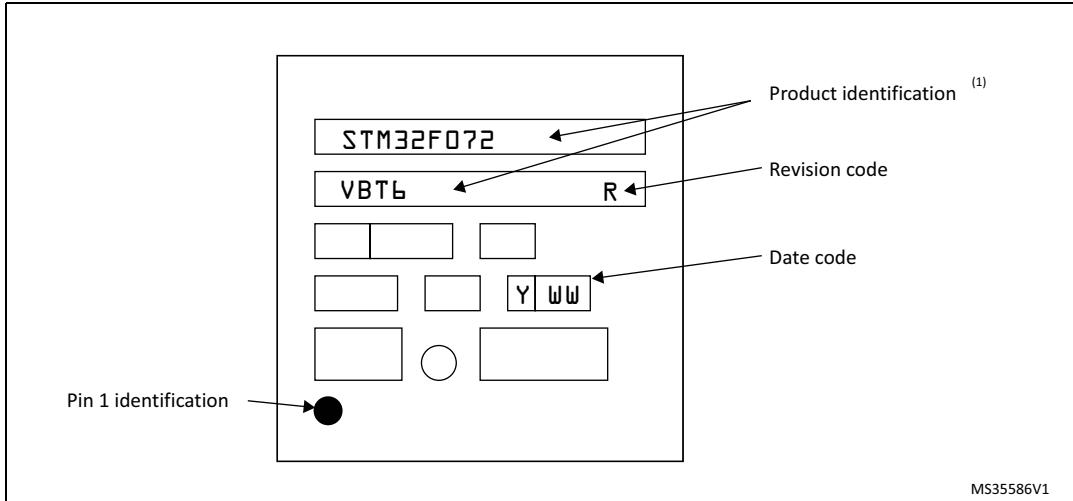
Figure 29. Maximum V_{REFINT} scaler startup time from power down

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 40. LQFP100 package marking example



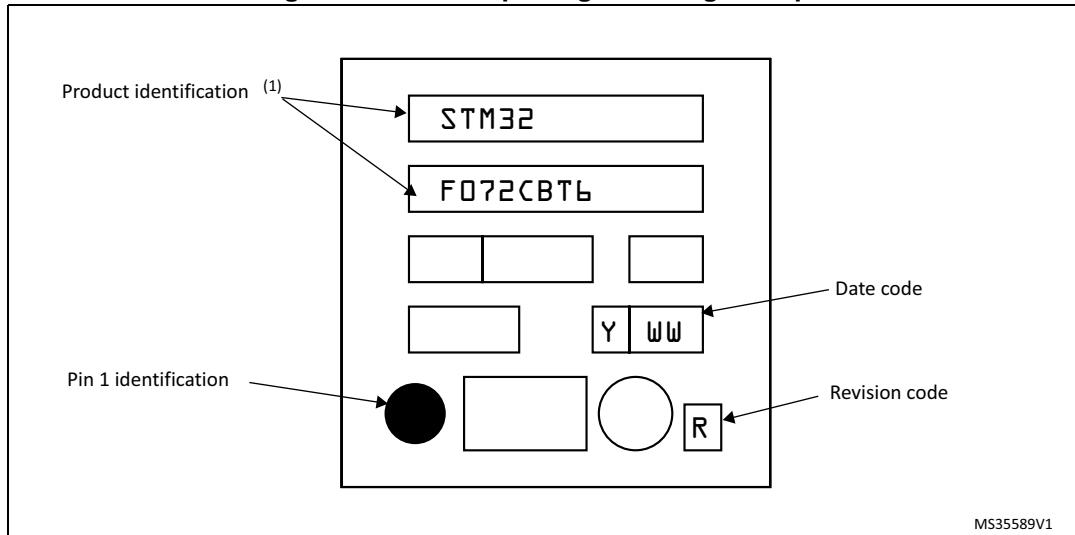
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 51. LQFP48 package marking example



MS35589V1

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F072x8/xB at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum temperature $T_{Amax} = 82^\circ\text{C}$ (measured according to JESD51-2), $I_{DDmax} = 50\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 20 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$ and maximum 8 I/Os used at the same time in output at low level with $I_{OL} = 20\text{ mA}$, $V_{OL} = 1.3\text{ V}$

$$P_{INTmax} = 50\text{ mA} \times 3.5\text{ V} = 175\text{ mW}$$

$$P_{IOmax} = 20 \times 8\text{ mA} \times 0.4\text{ V} + 8 \times 20\text{ mA} \times 1.3\text{ V} = 272\text{ mW}$$

This gives: $P_{INTmax} = 175\text{ mW}$ and $P_{IOmax} = 272\text{ mW}$:

$$P_{Dmax} = 175 + 272 = 447\text{ mW}$$

Using the values obtained in [Table 80](#) T_{Jmax} is calculated as follows:

- For LQFP64, 45°C/W

$$T_{Jmax} = 82^\circ\text{C} + (45^\circ\text{C/W} \times 447\text{ mW}) = 82^\circ\text{C} + 20.115^\circ\text{C} = 102.115^\circ\text{C}$$

This is within the range of the suffix 6 version parts ($-40 < T_J < 105^\circ\text{C}$).

In this case, parts must be ordered at least with the temperature range suffix 6 (see [Section 8: Ordering information](#)).

Note:

With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 7).

$$\text{Suffix 6: } T_{Amax} = T_{Jmax} - (45^\circ\text{C/W} \times 447\text{ mW}) = 105 - 20.115 = 84.885^\circ\text{C}$$

$$\text{Suffix 7: } T_{Amax} = T_{Jmax} - (45^\circ\text{C/W} \times 447\text{ mW}) = 125 - 20.115 = 104.885^\circ\text{C}$$

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum temperature $T_{Amax} = 100^\circ\text{C}$ (measured according to JESD51-2), $I_{DDmax} = 20\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 20 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$

$$P_{INTmax} = 20\text{ mA} \times 3.5\text{ V} = 70\text{ mW}$$

$$P_{IOmax} = 20 \times 8\text{ mA} \times 0.4\text{ V} = 64\text{ mW}$$

This gives: $P_{INTmax} = 70\text{ mW}$ and $P_{IOmax} = 64\text{ mW}$:

$$P_{Dmax} = 70 + 64 = 134\text{ mW}$$

Thus: $P_{Dmax} = 134\text{ mW}$

Using the values obtained in [Table 80](#) $T_{J\max}$ is calculated as follows:

- For LQFP64, 45 °C/W

$$T_{J\max} = 100 \text{ }^{\circ}\text{C} + (45 \text{ }^{\circ}\text{C/W} \times 134 \text{ mW}) = 100 \text{ }^{\circ}\text{C} + 6.03 \text{ }^{\circ}\text{C} = 106.03 \text{ }^{\circ}\text{C}$$

This is above the range of the suffix 6 version parts ($-40 < T_J < 105 \text{ }^{\circ}\text{C}$).

In this case, parts must be ordered at least with the temperature range suffix 7 (see [Section 8: Ordering information](#)) unless we reduce the power dissipation in order to be able to use suffix 6 parts.

Refer to [Figure 55](#) to select the required temperature range (suffix 6 or 7) according to your temperature or power requirements.

Figure 55. LQFP64 P_D max versus T_A

